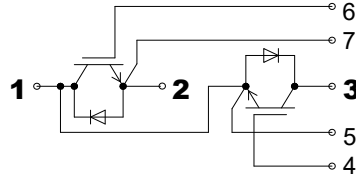


SGG300T65UC2

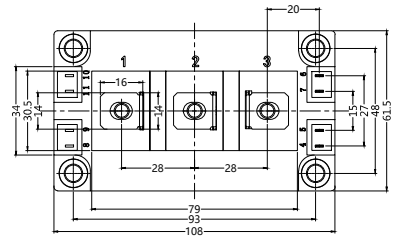
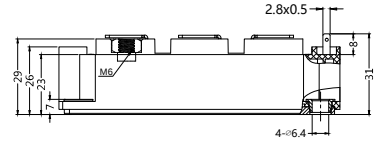
IGBT Modules



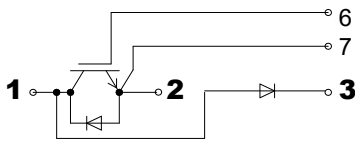
**SGG300T65UC2
(Half Bridge)**



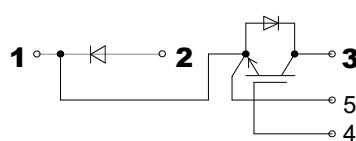
Dimensions in mm (1mm = 0.0394")



**SGD300T65UC2
(Boost Chopper)**



**SDG300T65UC2
(Buck Chopper)**



$T_C = 25^\circ\text{C}$, unless otherwise specified

Symbol	Conditions	Values	Units
IGBT			
V_{CES}		650	V
I_C	$T_C=25(100)^\circ\text{C}$	600(300)	A
I_{CRM}	$T_C=25^\circ\text{C}, t_P=1\text{ms}$	900	A
V_{GES}		± 20	V
T_{Vj}		$-40 \dots +175$	$^\circ\text{C}$
InverseDiode			
$I_F = -I_C$	$T_C=25(80)^\circ\text{C}$	600(300)	A
I_{FRM}	$T_C=25^\circ\text{C}, t_P=1\text{ms}$	900	A
I_{FSM}	$t_P=10\text{ms}; \sin 180^\circ; T_J=25^\circ\text{C}$	900	A
V_{RRM}		650	V
Module			
$I_{t(RMS)}$	$T_{terminal} = 80^\circ\text{C}$	300	A
T_{stg}		$-40 \sim 125$	$^\circ\text{C}$
V_{Isol}	AC, 1min	4000	V

Features

- Trench Field Stop Technology
- Low switching losses
- Switching frequency up to 30kHz
- Square RBSOA, no latch up
- High short circuit capability
- Positive temperature coefficient for easy paralleling
- MOS input, voltage controlled
- Soft switching FWD diode Technology
- Package with copper base plate
- Isolation voltage 4000 V

Application

- AC and DC motor control
- AC servo and robot drives
- Power supplies
- Welding inverters



Advantages

- Space and weight savings
- Reduced protection circuits

Sirectifier®

SGG300T65UC2

IGBT Modules

Characteristics

T_c = 25°C, unless otherwise specified

Symbol	Conditions	min.	typ.	max.	Units
IGBT					
V _{GE(th)}	V _{GE} =V _{CE} , I _C =3mA	4.5	5.0	6.0	V
I _{CES}	V _{GE} =0; V _{CE} =V _{CES} ; T _j =25°C			0.05	mA
V _{CE(TO)}	T _j =25°C		0.9		V
r _{CE}	V _{GE} =15V, T _j =25(150)°C		1.8(2.7)		mΩ
V _{CE(sat)}	I _C =300A; V _{GE} =15V; chip level		1.65	2.10	V
C _{ies}	under following conditions V _{GE} =0, V _{CE} =25V, f=1MHz		18		nF
C _{oes}			0.80		
C _{res}			0.40		
L _{CE}				30	nH
R _{CC'+EE'}	res., terminal-chip T _c =25(125)°C		0.65(1.09)		mΩ
t _{d(on)}	under following conditions: V _{CC} =300V, I _C =300A R _{Gon} =R _{Goff} =1Ω, T _j =150°C V _{GE} =±15V		660		ns
t _r			79		ns
t _{d(off)}			105		ns
t _f			60		ns
E _{on} /E _{off} /E _{ts}			3.6/8.4/6.4		mJ
Inverse Diode under following conditions:					
V _F = V _{EC}	I _F =300A; V _{GE} =0V; T _j =25°C		1.50		V
V _(FO)	T _j =25(125)°C		1.2(0.90)	1.4(1.1)	V
r _F	T _j =25(125)°C		17(24)	21(27)	mΩ
I _{RM}	I _F =300A; T _j =25°C		12.6		A
Q _{rr}	di/dt=100A/us		0.45		uC
E _{rr}	V _{GE} = ±15V		12.8		mJ
Thermal Characteristics					
R _{th(j-c)}	per IGBT			0.41	K/W
R _{th(j-c)D}	per Inverse Diode			0.89	K/W
R _{th(c-s)}	per module			0.28	K/W
Mechanical Data					
M _s	to heatsink M6	3		5	Nm
M _t	to terminals M6	2.5		5	Nm
Weight	typical			325	g

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IGBT Modules

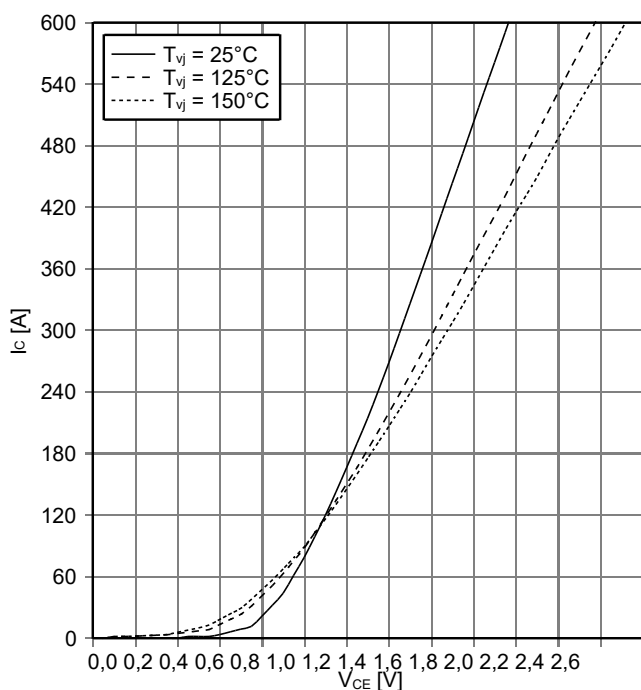


Fig.1 Output characteristic IGBT, Inverter (typical)
 $I_C = f(V_{CE})$ $V_{GE} = 15V$

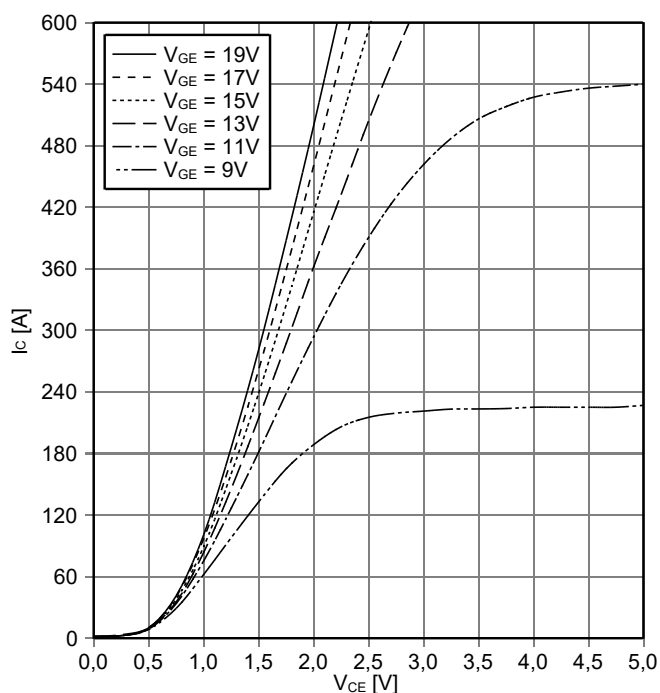


Fig.2 Output characteristic IGBT, Inverter (typical)
 $I_C = f(V_{CE})$ $T_{vj} = 150^\circ C$

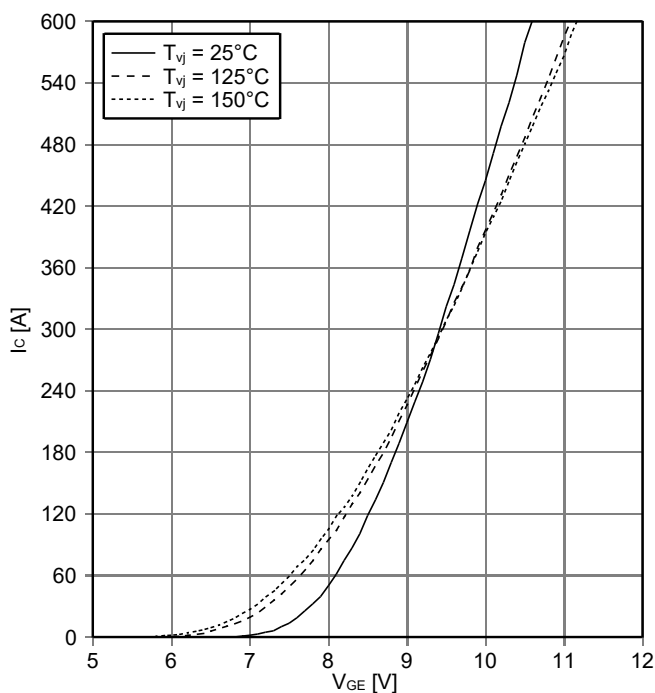


Fig.3 Transfer characteristic IGBT, Inverter (typical)
 $I_C = f(V_{GE})$ $V_{CE} = 20V$

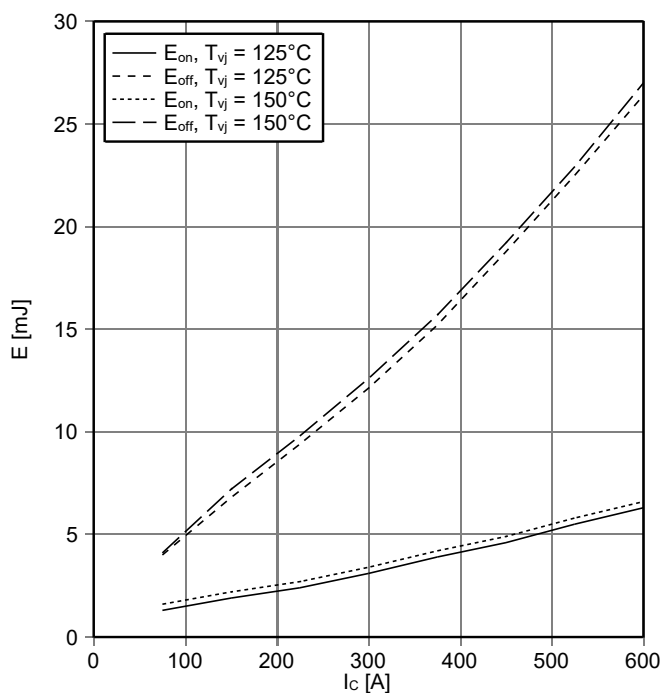


Fig.4 Switching losses IGBT, Inverter (typical)
 $E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15V$, $R_{Gon} = 2.4\Omega$, $R_{Goff} = 2.4\Omega$, $V_{CE} = 300V$

SGG300T65UC2

IGBT Modules

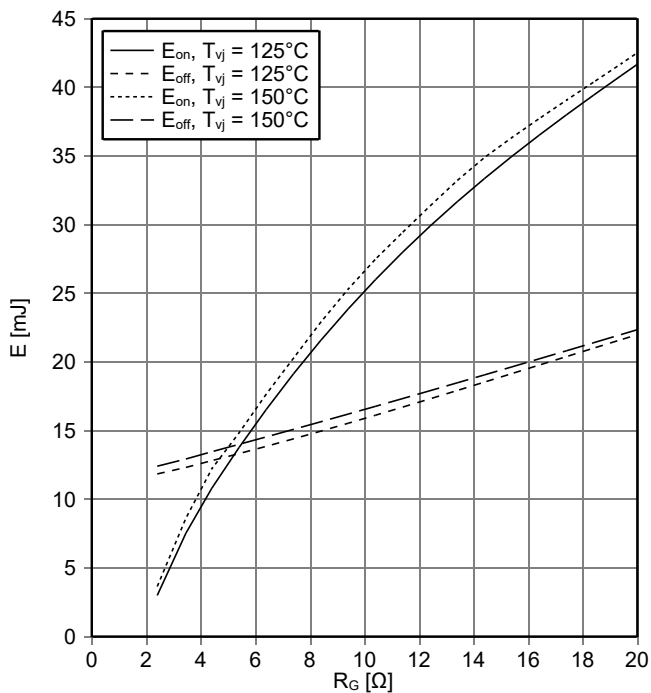


Fig.5 Switching losses IGBT, Inverter (typical)

$E_{on}=f(R_G), E_{off}=f(R_G)$
 $V_{GE}=\pm 15V, I_C=300A, V_{CE}=300V$

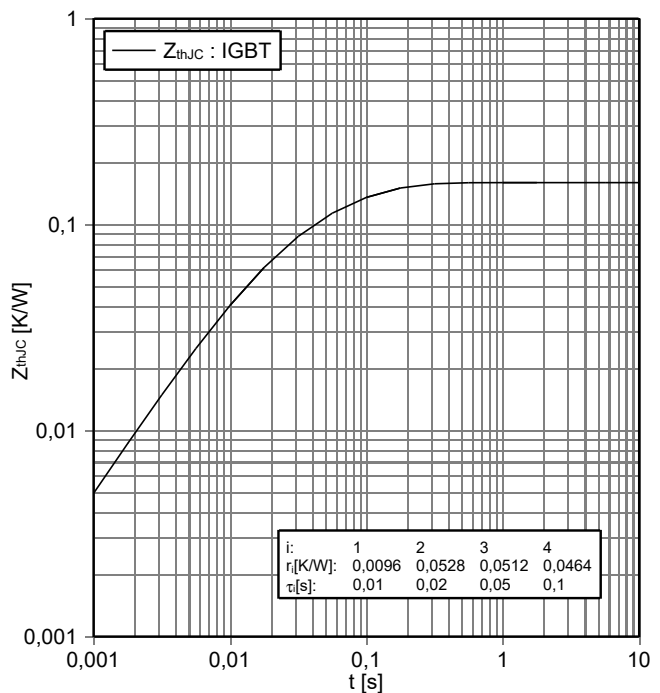


Fig.6 Transient thermal impedance IGBT, Inverter

$Z_{thJC}=f(t)$

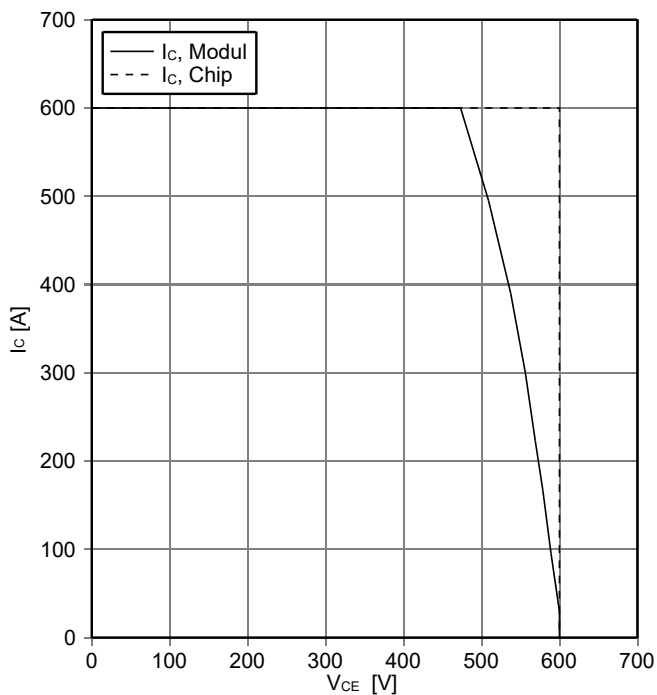


Fig.7 Reverse bias safe operating area IGBT, Inverter (RBSOA)

$I_C=f(V_{CE}) V_{GE}=\pm 15V, R_{Goff}=2.4\Omega, T_{vj}=150^\circ C$

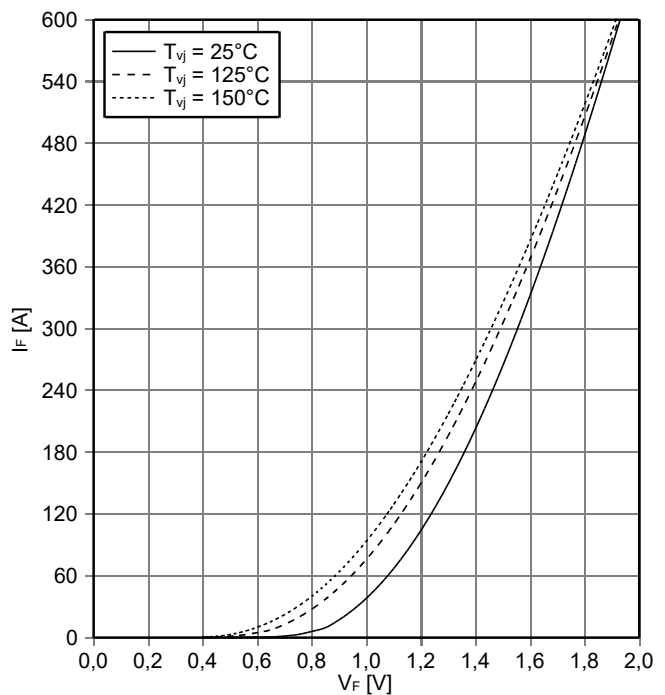


Fig.8 Forward characteristic of Diode, Inverter (typical) $I_F=f(V_F)$

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IGBT Modules

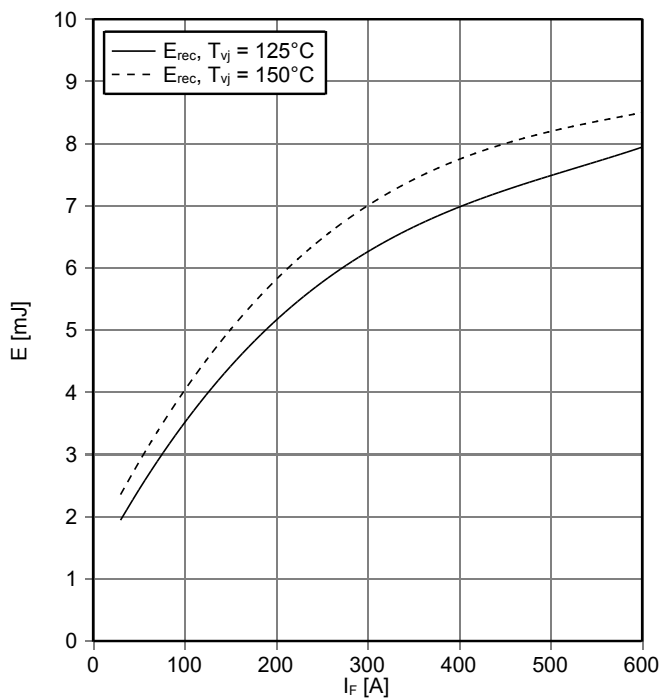


Fig.9 Switching losses Diode, Inverter (typical)
 $E_{rec}=f(I_F)$ $R_{Gon}=2.4\Omega$, $V_{CE}=300V$

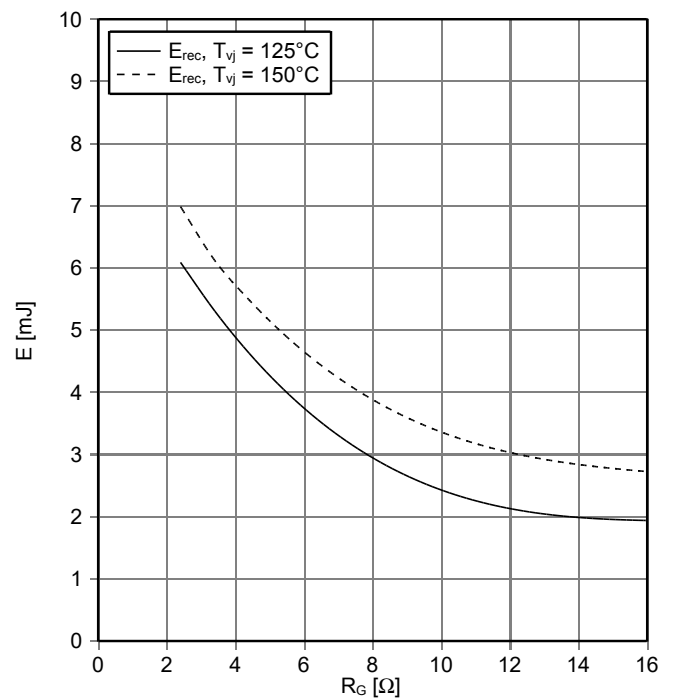


Fig.10 Switching losses Diode, Inverter (typical)
 $E_{rec}=f(R_G)$ $I_F=300A$, $V_{CE}=300V$

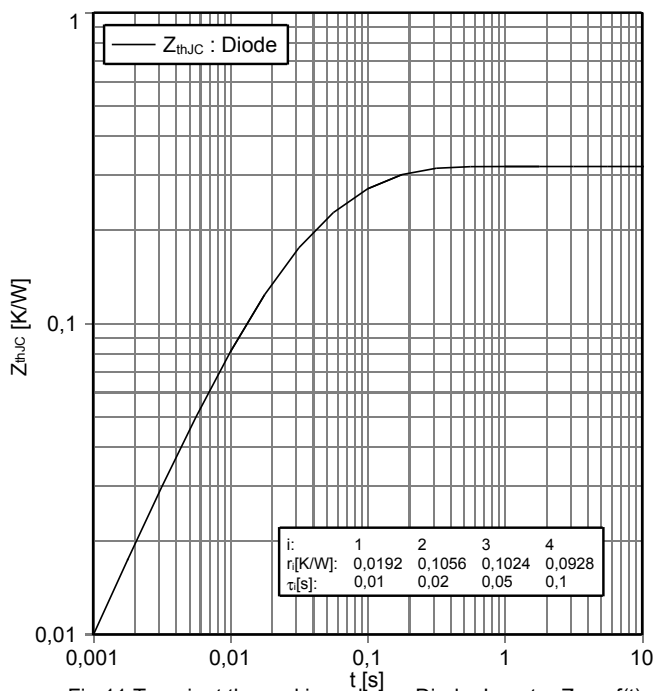


Fig.11 Transient thermal impedance Diode, Inverter $Z_{thJC}=f(t)$